The Application of the Continuous Anodic Oxidation Technique for the Evaluation of State-of-the-Art Front-End Structures

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Spansion Presentation

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Outline

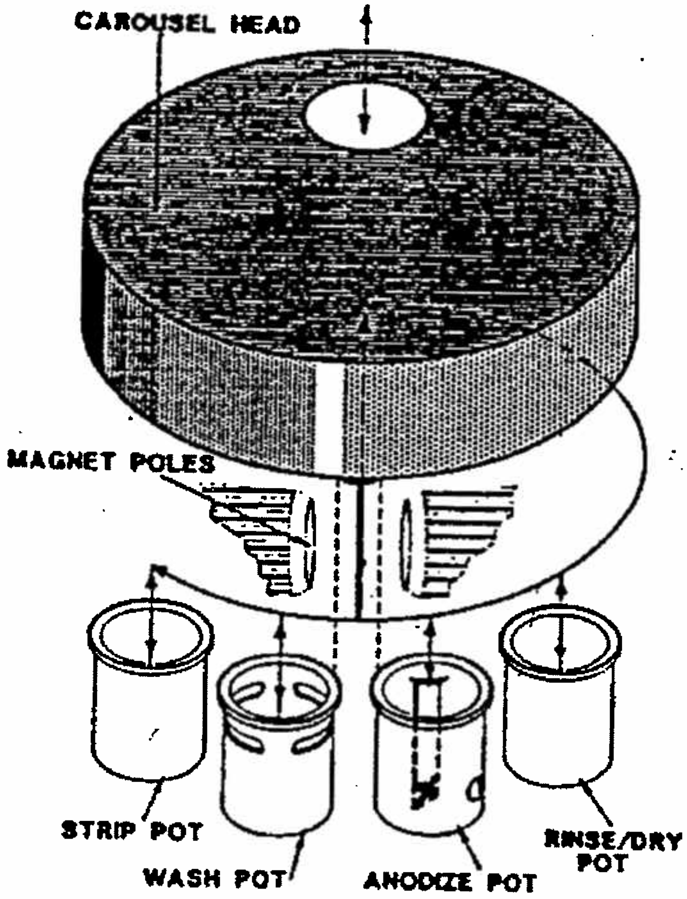
- Introduction
- A.S.T.M. Algorithm
- Defect Scattering Contribution to Mobility
- Hall Scattering Factor
- Depletion Effect
- Anodic Oxide Breakdown
- Comparison of CAOT DHE with SIMS and SRP
- Application of CAOT DHE for Doped Polysilicon Films
- Conclusions

Doping Techniques and Thermal Treatments

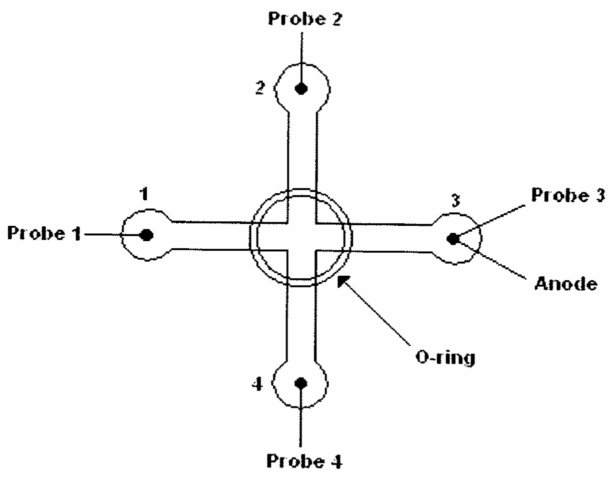
- Doping Techniques
  - Ion Implantation
  - Plasma Imersion
  - Cluster
  - Molecular
- Thermal Treatments
  - RTA
  - SPER
  - LSA (Laser Spike Anneal)
  - Flash (Arc-lamp fRTP or Xe-lamp FLA (flash lamp anneal))
  - DSA (Dynamic Surface Anneal)
  - Combinations

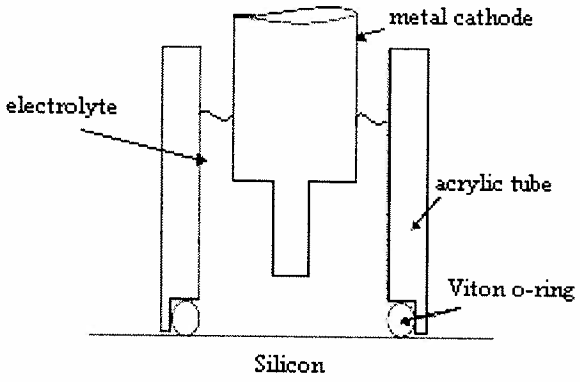
HL5900 Stripping Hall System

(BIORAD MICROSCIENCE)

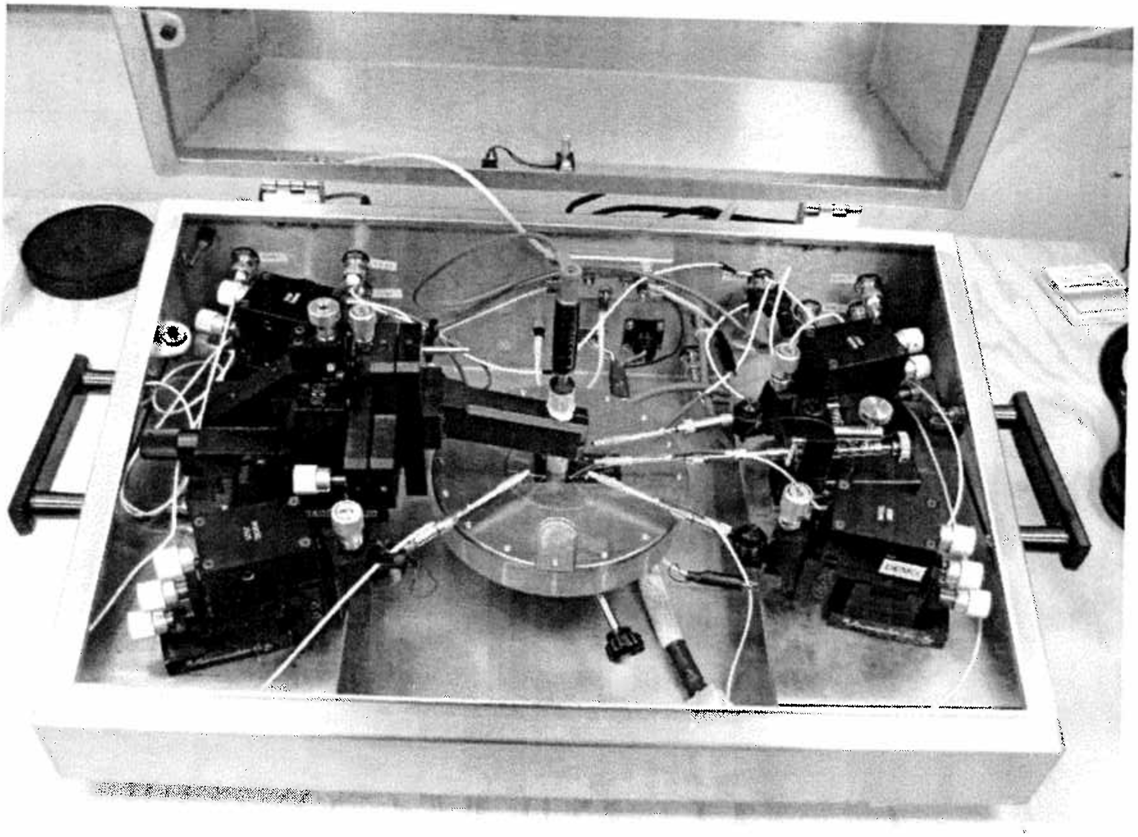


CAOT Set-Up

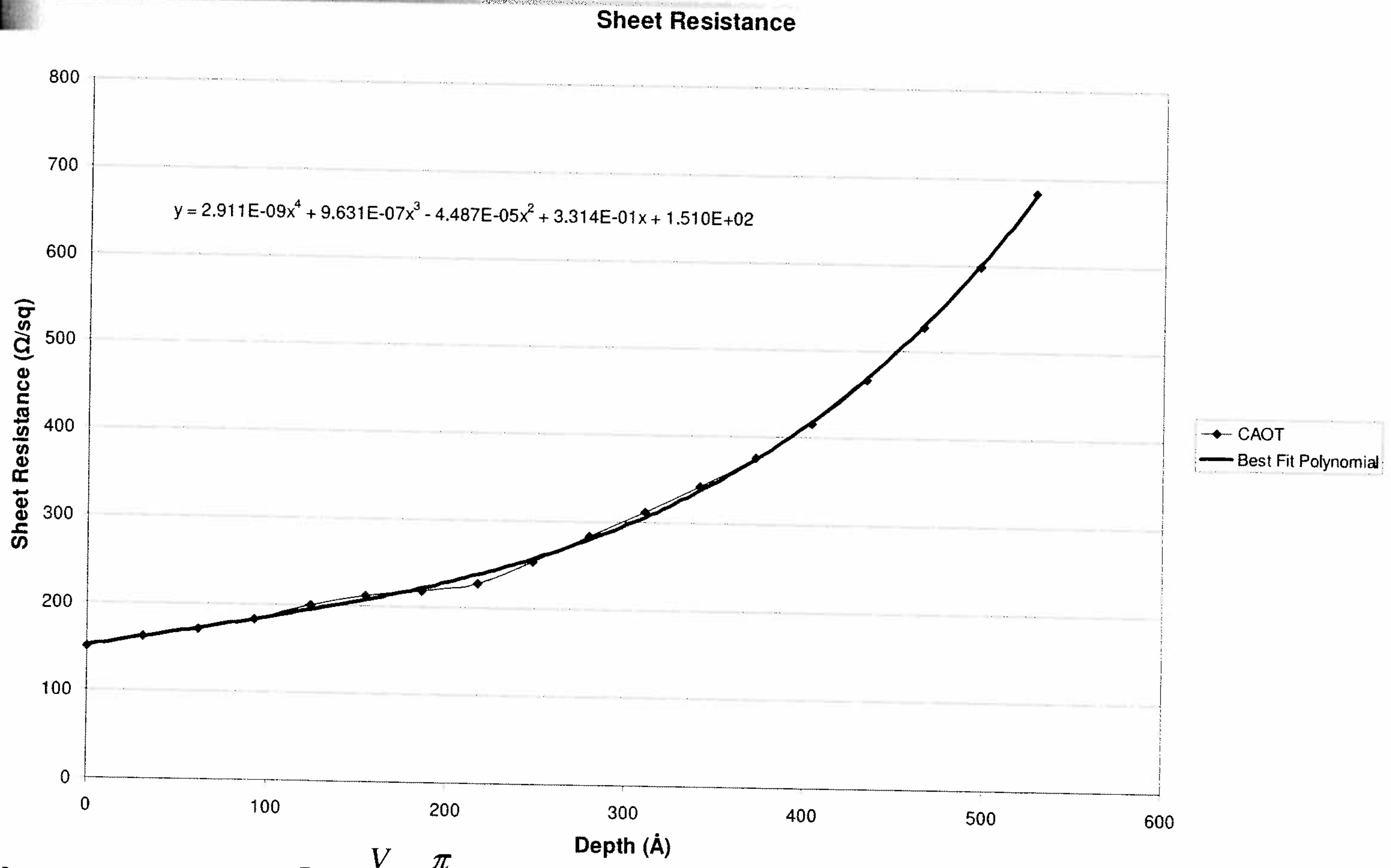

Probe 2
2
1
Probe 1
3
Probe 3
Anode
O-ring
4
Probe 4


metal cathode
electrolyte
acrylic tube
Viton o-ring
Silicon

CAOT Probing Station

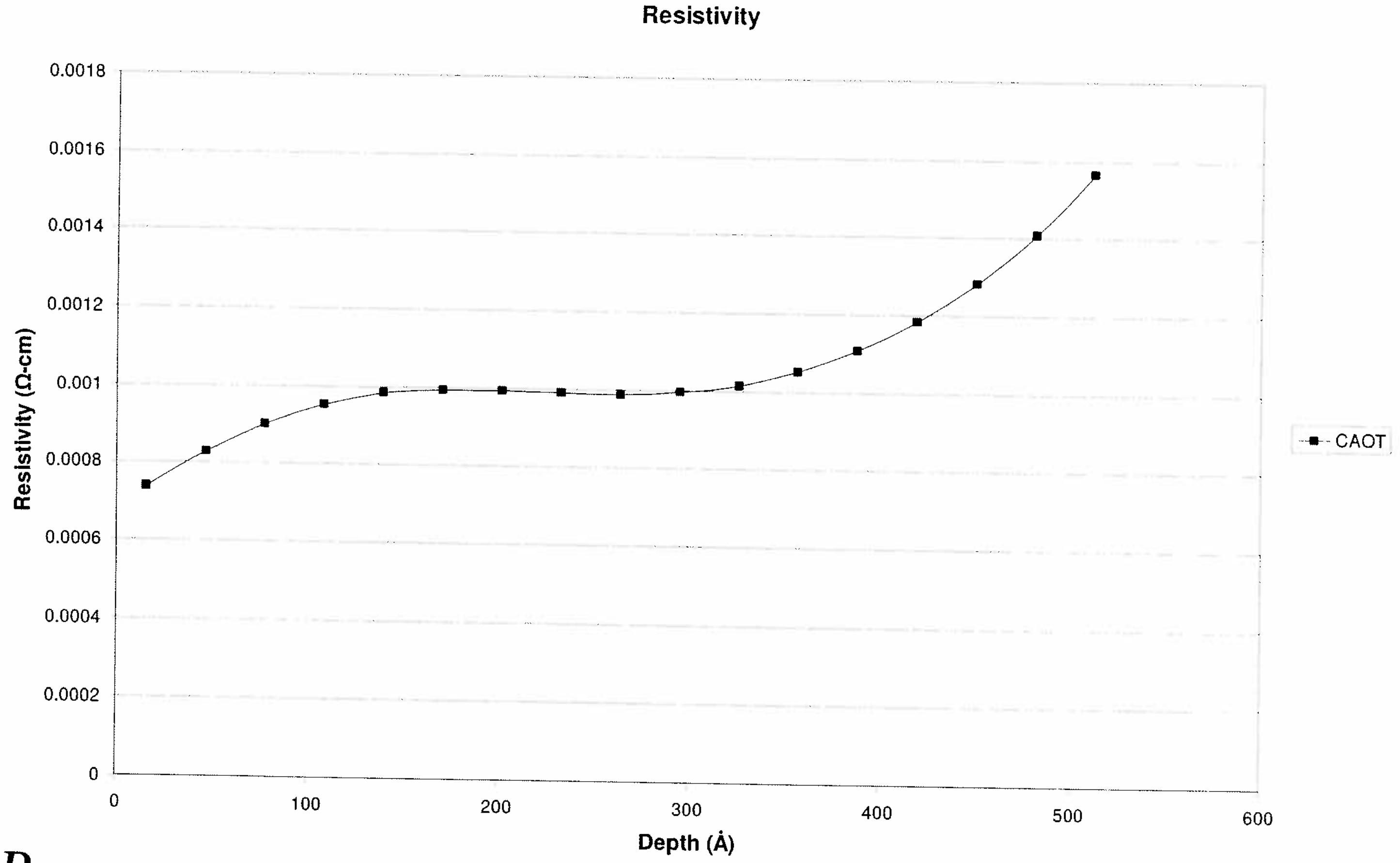


Sheet Resistance



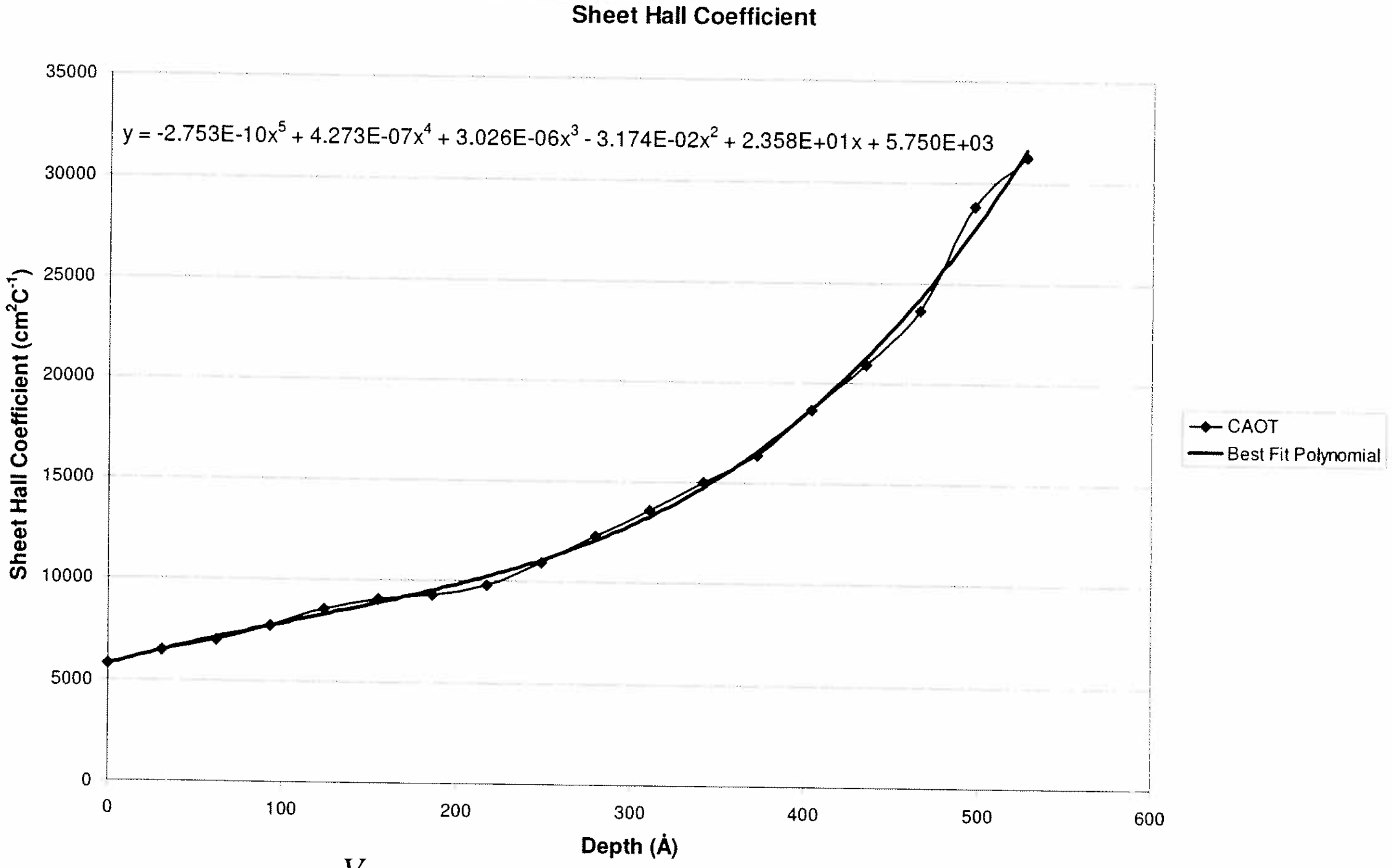
Direct Measurements $R_S = \frac{V}{I} \cdot \frac{\pi}{\ln 2}$

Resistivity



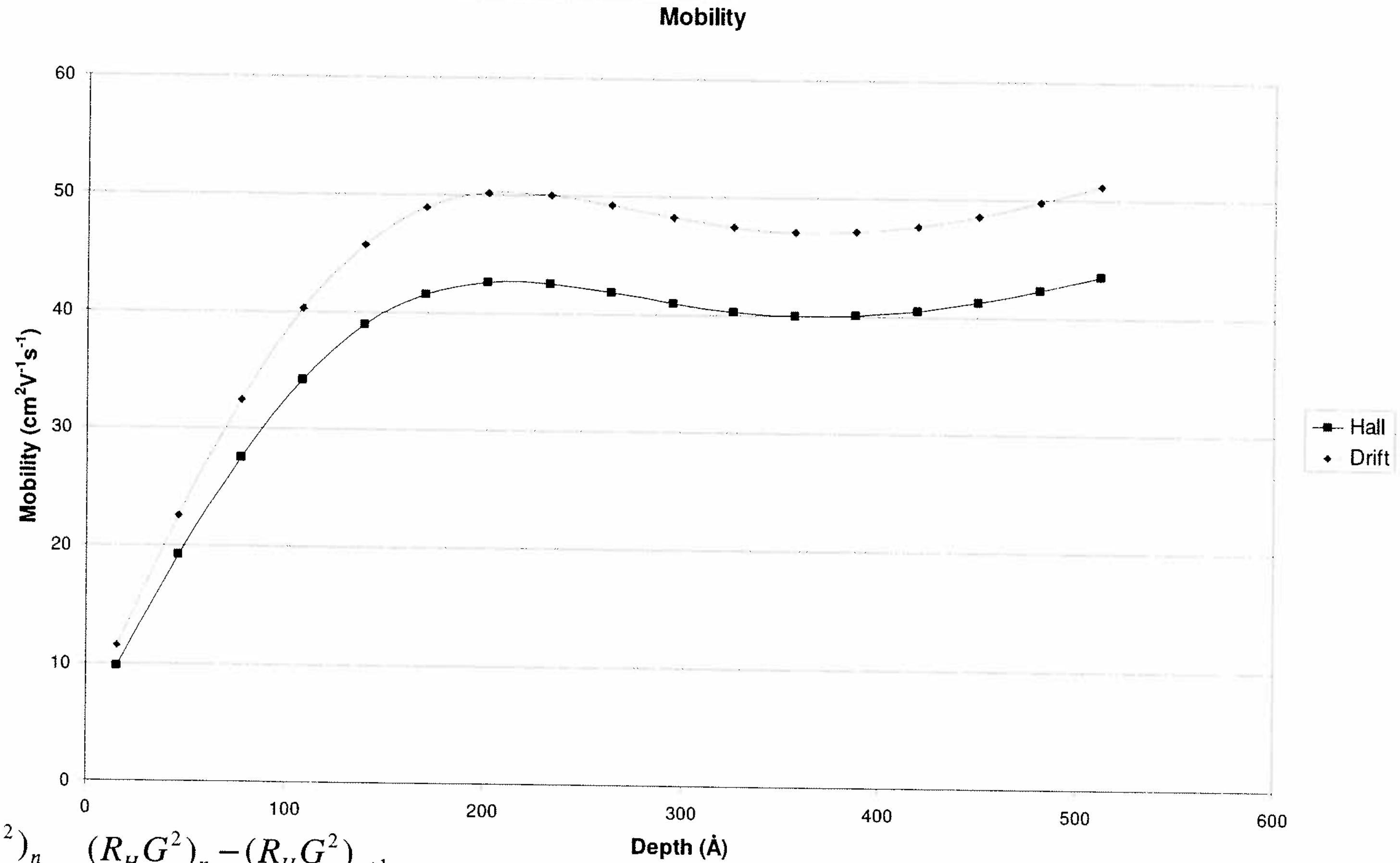
$$\rho = \Delta x \Delta R_s$$

Sheet Hall Coefficient



Direct Measurements $R_{HS} = \frac{V}{I \cdot B}$

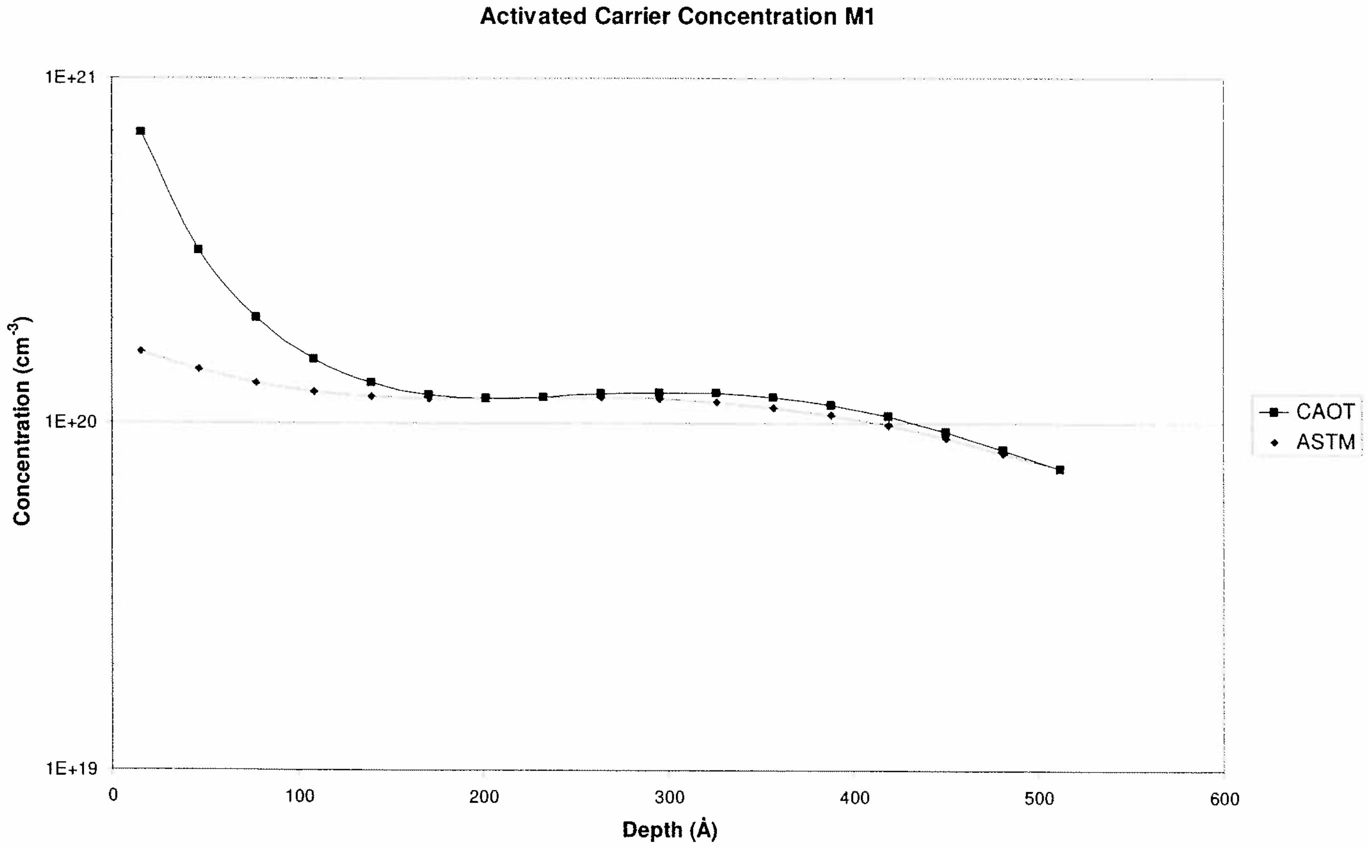
Mobility



$$\mu_{Drift} = \frac{\mu_H}{r_H}$$

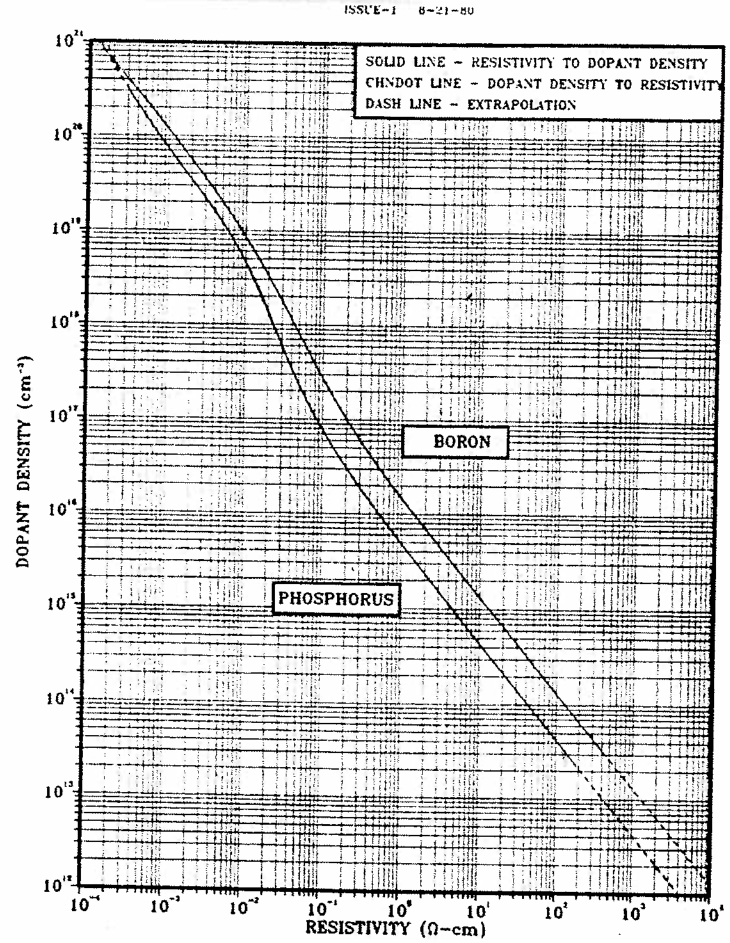
$$\mu_H = \frac{\Delta(R_H G^2)_n}{\Delta(G)_n} = \frac{(R_H G^2)_n - (R_H G^2)_{n+1}}{(G)_n - (G)_{n+1}}$$

Concentration



$$n = \frac{1}{\rho \mu q}$$

Conversion Between Resistivity and Dopant Density



Designation: F 723 – 99

Standard Practice for
Conversion Between Resistivity and Dopant Density for Boron-Doped, Phosphorus-Doped, and Arsenic-Doped Silicon [1]

n-type

$$N = \frac{6.242\times10^{18}}{\rho}\times10^{Z} \quad [cm^{-3}]$$

where

$$Z = \frac{A_0 + A_1x + A_2x^2 + A_3x^3}{1+B_1x+B_2x^2+B_3x^3}$$

$x=\log_{10}\rho$

$A_0= -3.1083$

$A_1= -3.2626$

$A_2= -1.2196$

$A_3= -0.13923$

$B_1= 1.0265$

$B_2= 0.38755$

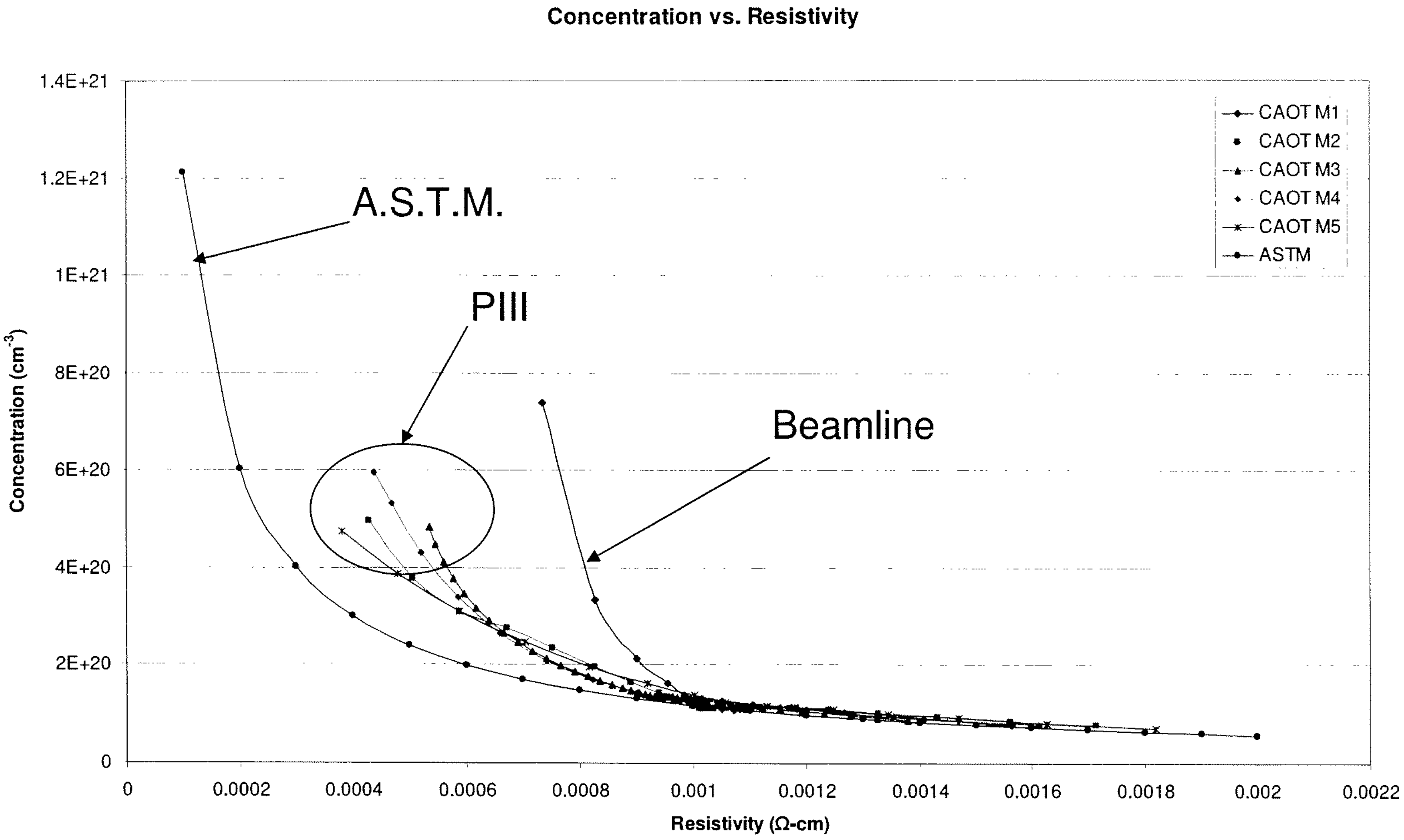
$B_3=0.041833$

p-type

$$P = \frac{1.330\times10^{16}}{\rho} + \frac{1.082\times10^{17}}{\rho\bullet(1+(54.56\bullet\rho)^{1.105})} \quad [cm^{-3}]$$

Standard Test Method for
Measuring Resistivity Profiles Perpendicular to the Surface of a Silicon Wafer Using a Spreading Resistance Probe [1]

X3.1.4 The silicon slices in the empirical study from which these conversion relations were derived, had a lowest resistivity value of 0.00086 Ω-cm for boron-doped silicon and 0.00055 Ω-cm for phosphorus-doped silicon. Caution should be taken when applying these conversion relations to resistivities near or below these values.



$$n = \frac{1}{\rho \cdot \mu \cdot q}$$

Defect Scattering Contribution to Mobility

$$\frac{1}{\mu_0} = \frac{1}{\mu_{ph}} + \frac{1}{\mu_{coul}}$$

For carrier concentrations > ~1E20cm-3 we can add the scattering contribution of crystal imperfections and complexes

$$\frac{1}{\mu} = \frac{1}{\mu_{ph}} + \frac{1}{\mu_{coul}} + \frac{1}{\mu_{def}}$$

$$\frac{1}{\mu} = \frac{1}{\mu_0} + \frac{1}{\mu_{def}}$$

$$\mu_{def} = \frac{\mu \cdot \mu_0}{\mu_0 - \mu}$$

μ=measured CAOT DHE mobility $(\frac{\mu_H}{r})$

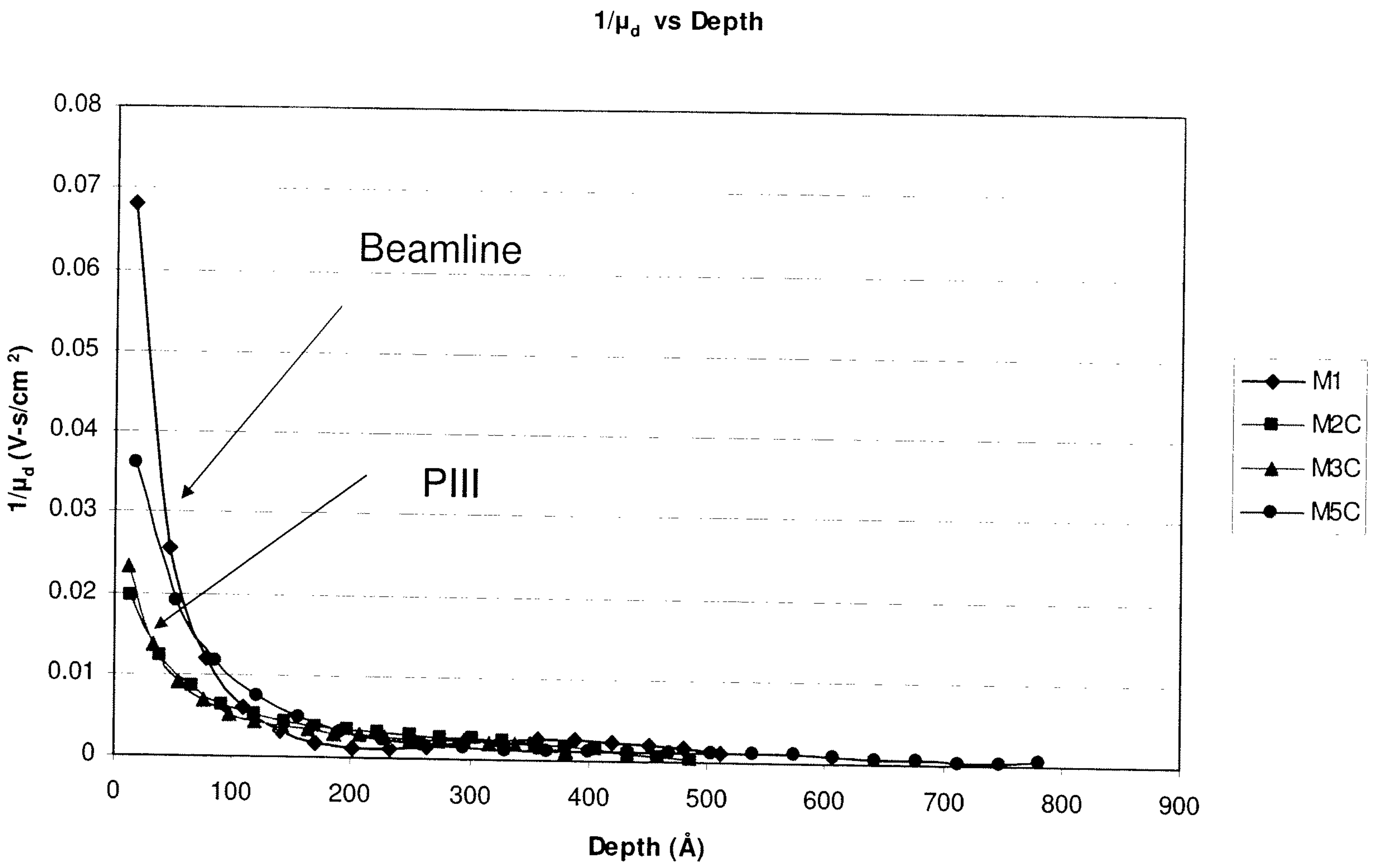
μ_0=mobility calculated from the A.S.T.M. conversion relation

μ_{def} =scattering component due to crystal imperfections and complexes

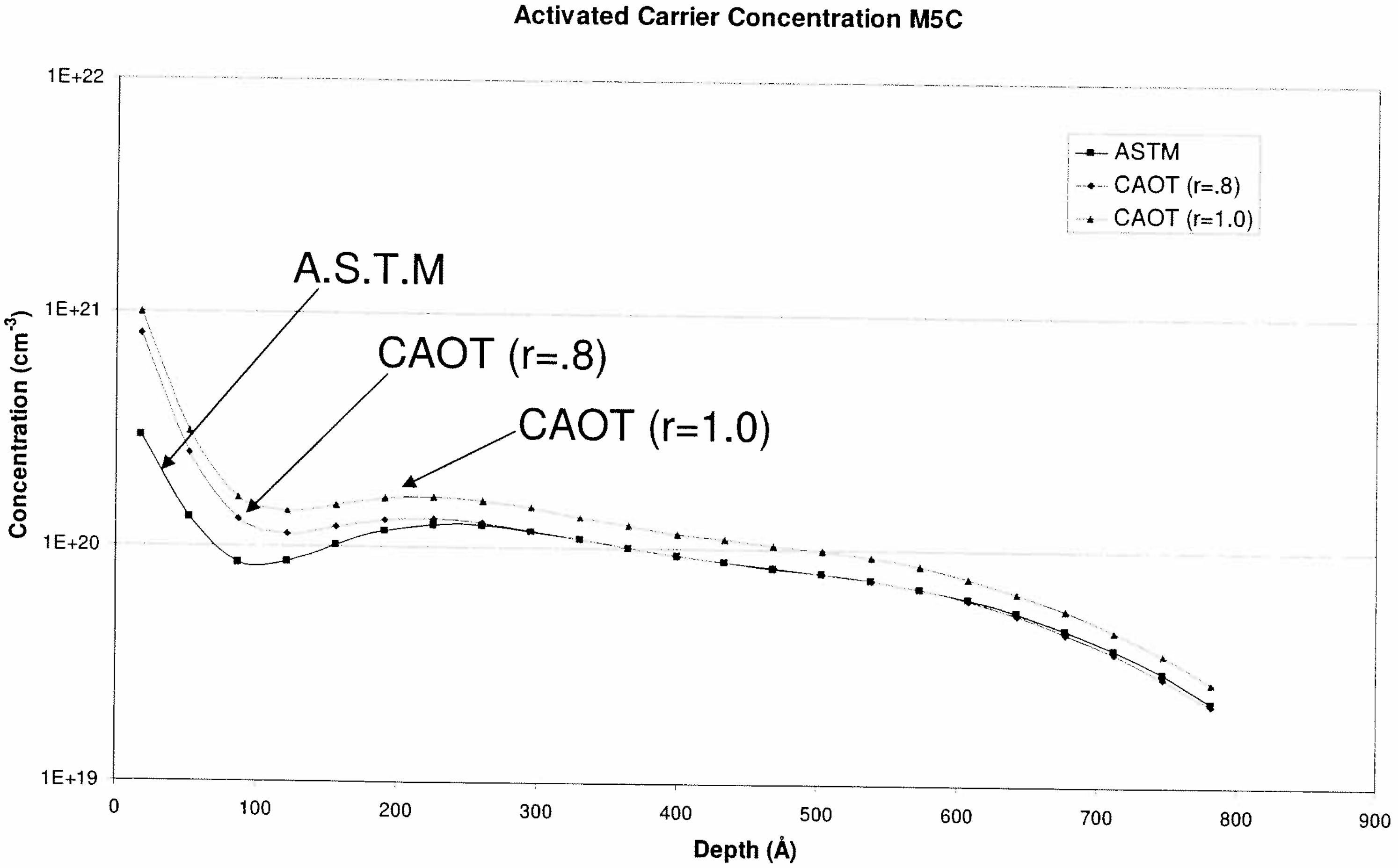
r=Hall scattering factor

Defect Scattering Contribution to Mobility (2)

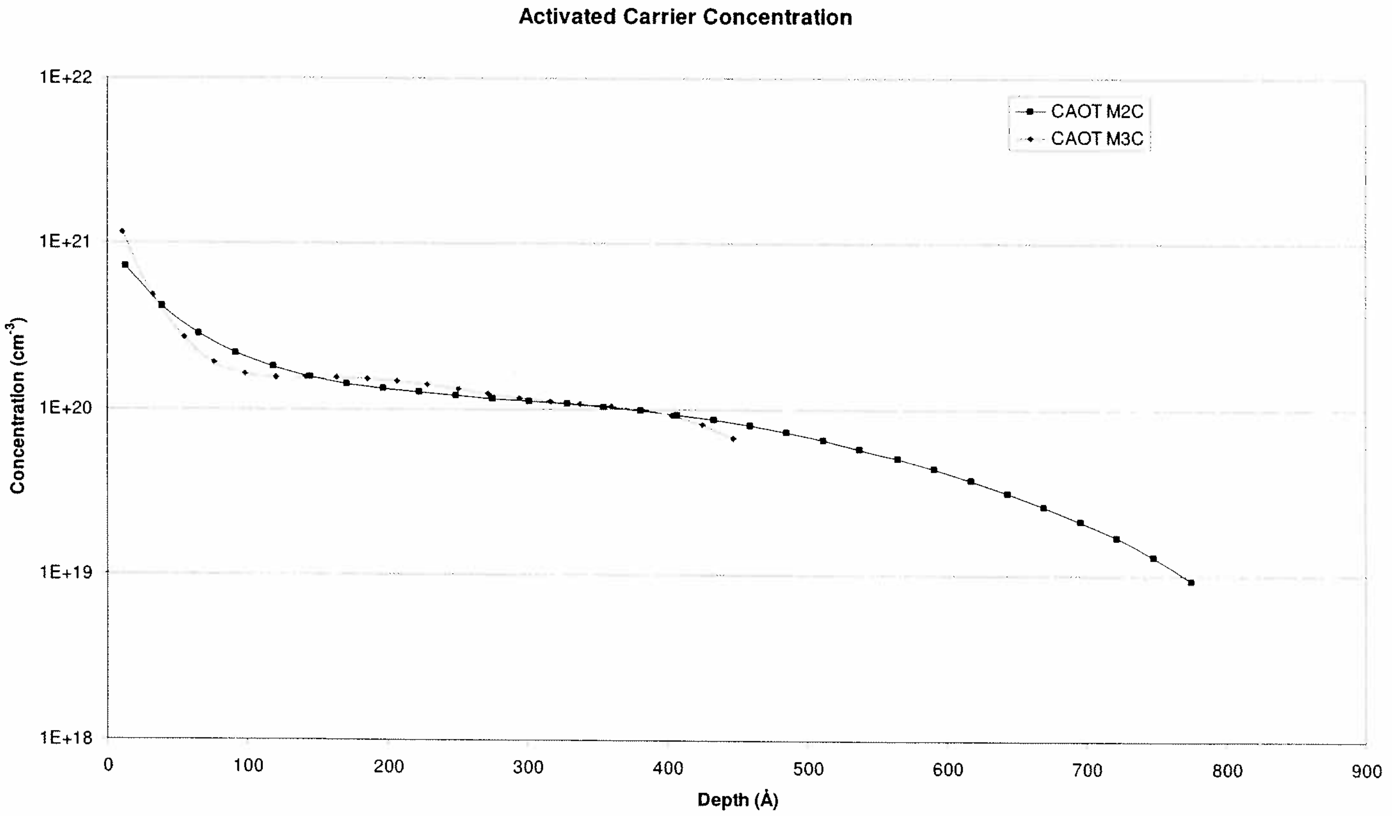
At present, several different doping techniques, such as beamline, PIII, cluster beams, and molecular beams together with various thermal activating processes are being studied as a means to satisfy ultra-shallow junction requirements for the coming generations of devices. In addition we have introduced various thermal treatments. The CAOT permits us to accurately determine the carrier concentration distribution, and the drift mobility characteristics of these competing technologies.


$1/\mu_d$ vs Depth
$1/\mu_d$ (V-s/cm ^{2})
0.08
0.07
0.06
0.05
0.04
0.03
0.02
0.01
0
0
100
200
300
400
500
600
700
800
900
Depth (Å)
Beamline
PIII
M1
M2C
M3C
M5C

Hall Scattering Factor

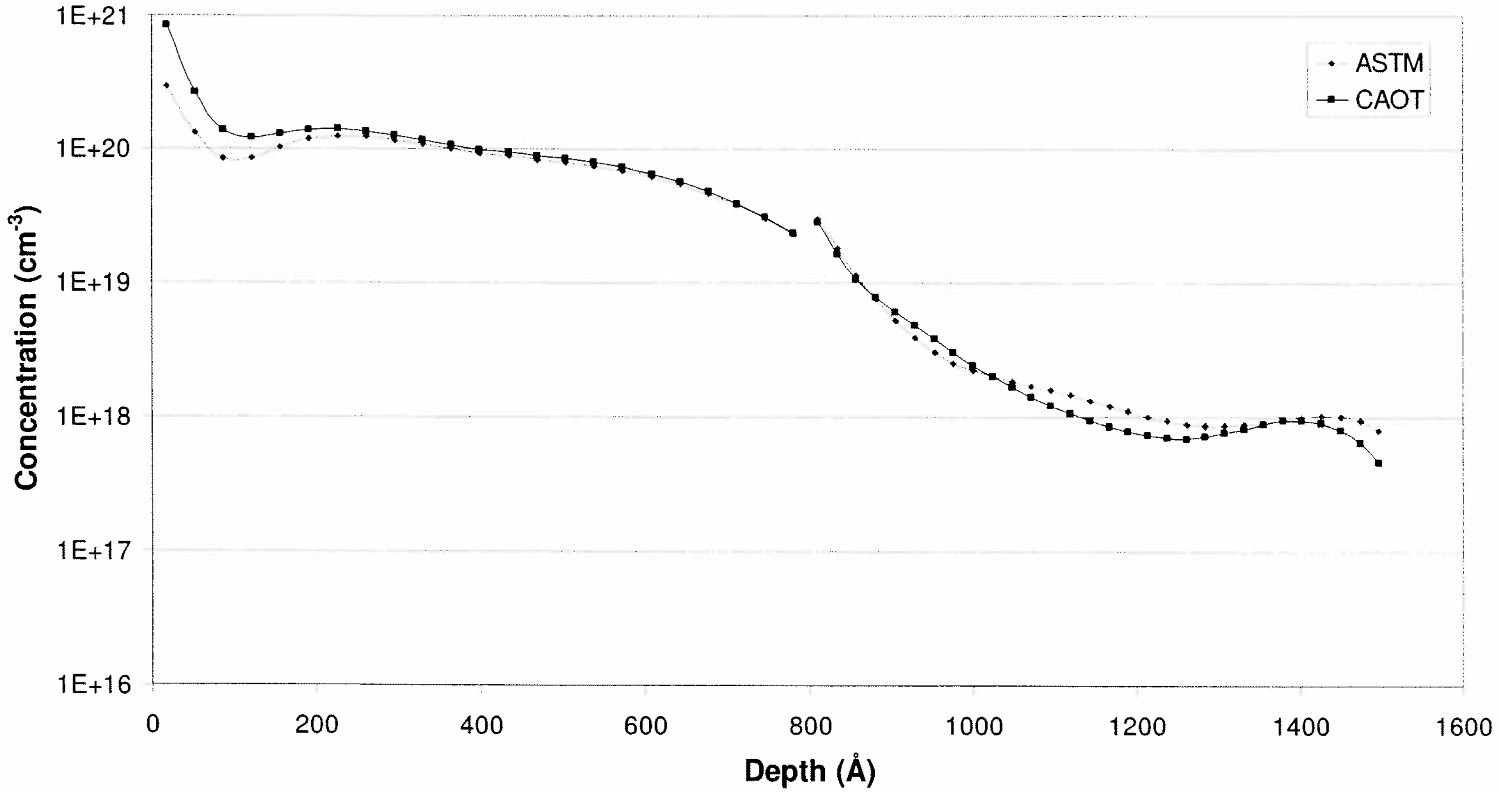


Depletion Effect

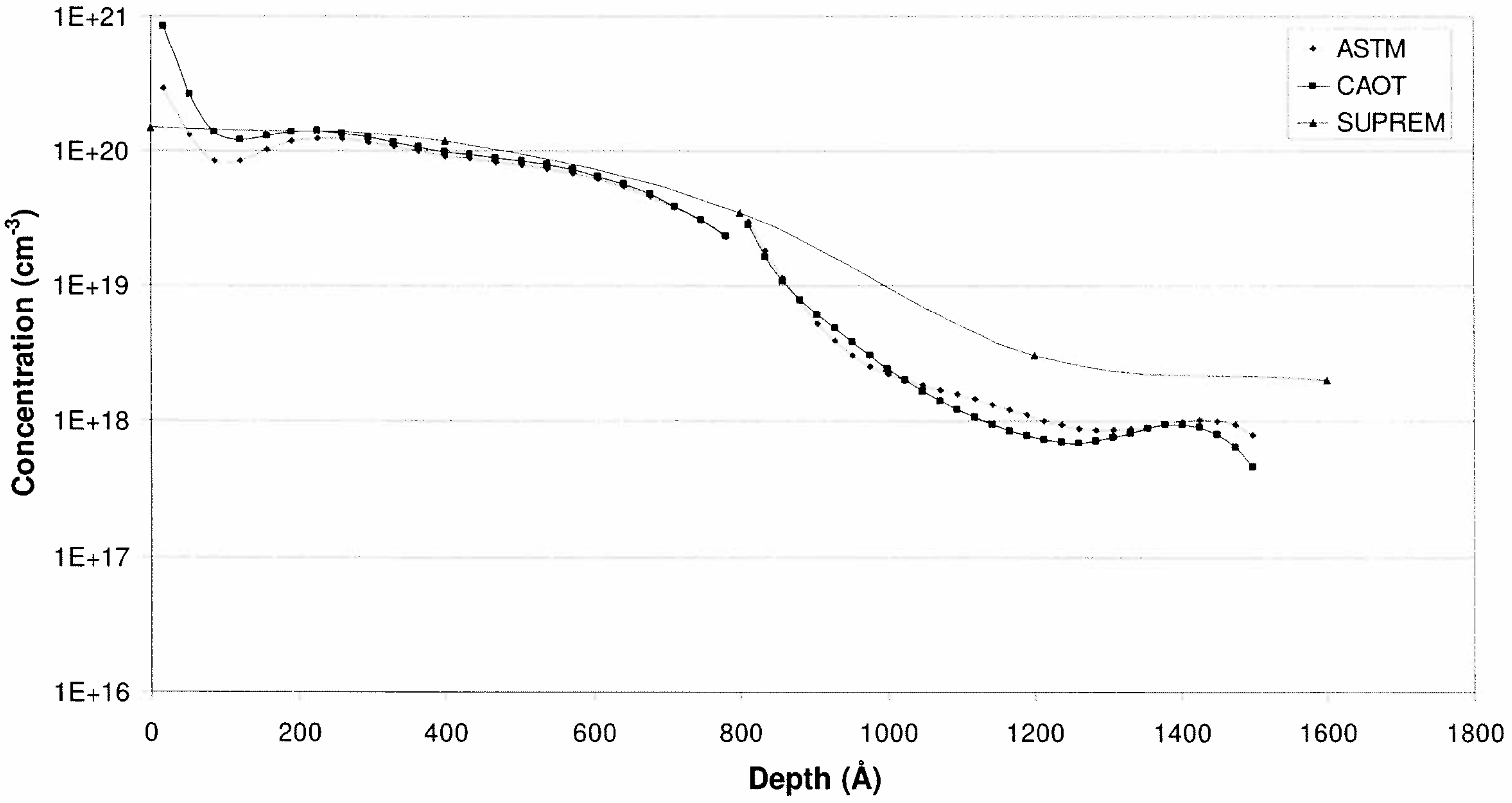


Anodic Oxide Breakdown

Activated Carrier Concentration M5C

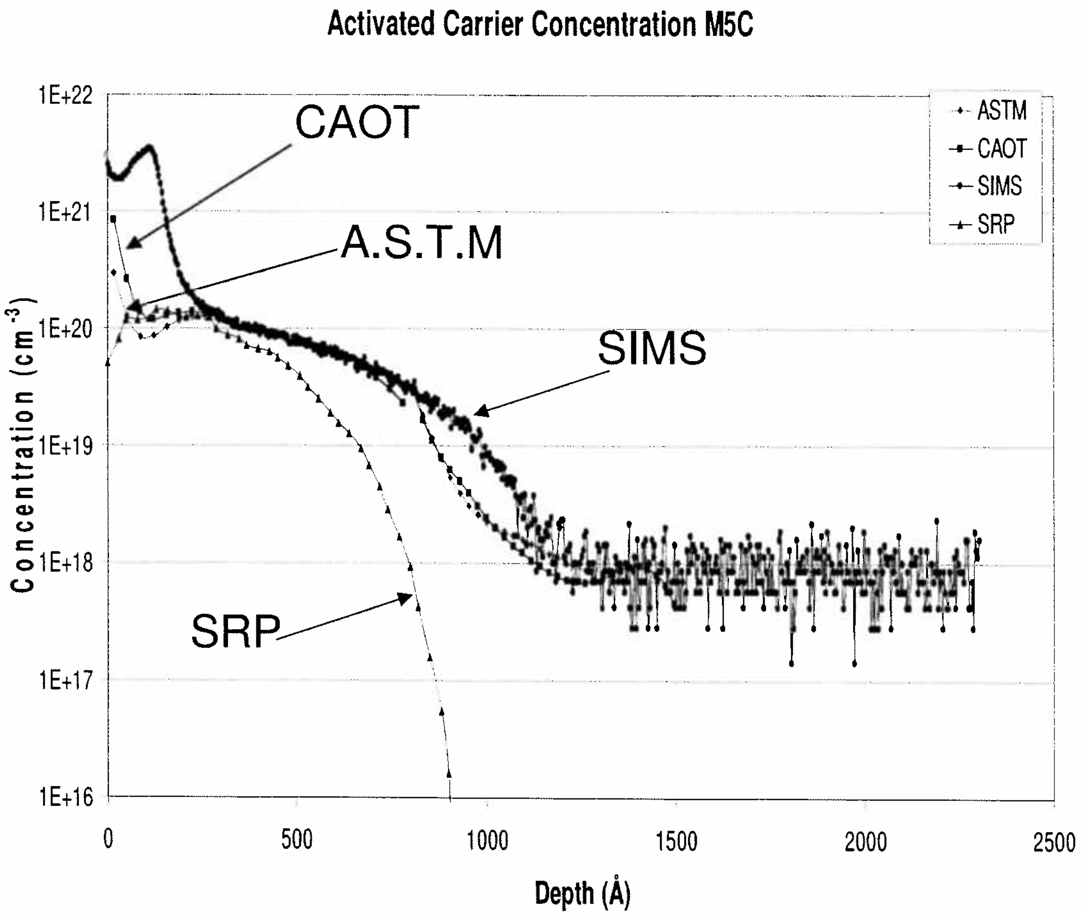


Anodic Oxide Breakdown (2)



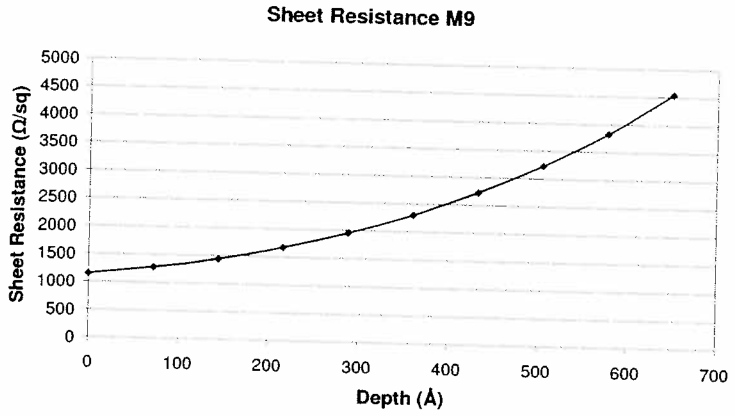
Activated Carrier Concentration M5C

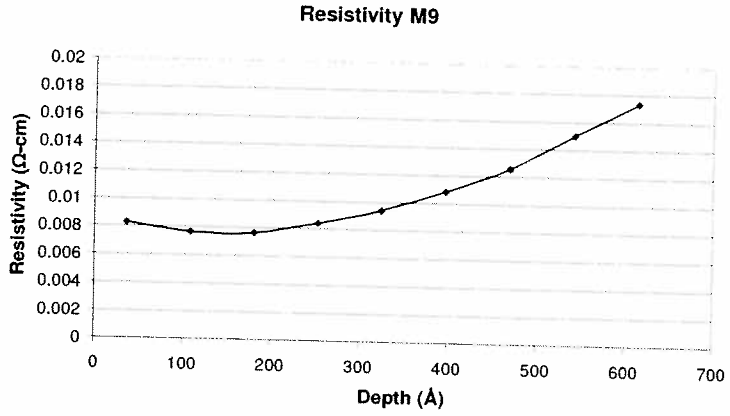
Comparison of CAOT DHE with SIMS and SRP Evaluations


Activated Carrier Concentration M5C

- •DHE tracks A.S.T.M. up to 1E20 cm^{-3}.
- •SRP carrier concentration too low at surface
- •SIMS at surface assumed constant B_{ss}.
- •DHE provides correct surface carrier concentration
- •Deactivation illustrated at ~100nm

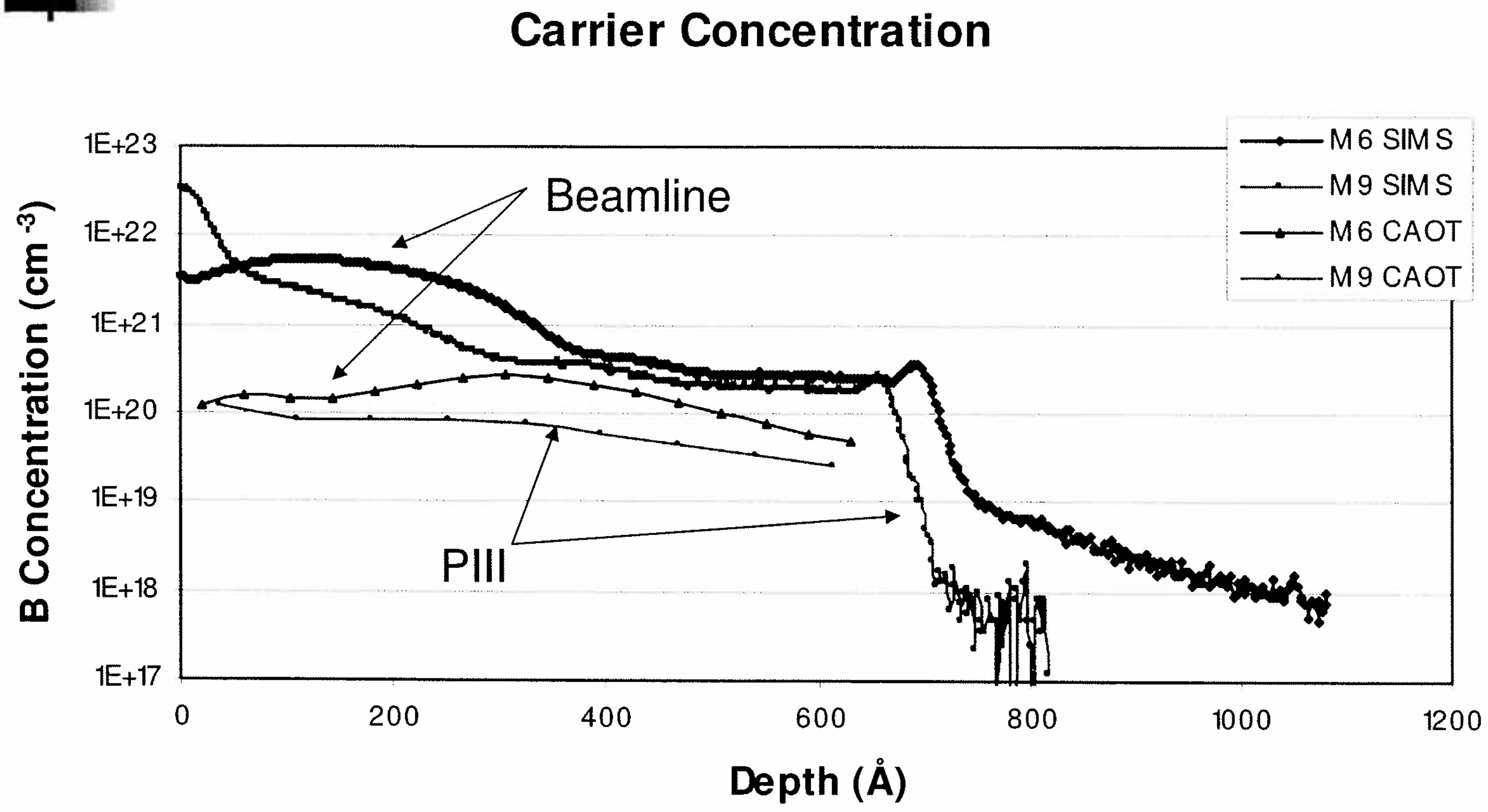
Application of CAOT DHE For Doped Polysilicon Films





	4pp	CAOT vdP	Integrated ρ	Initial	Final	$Rs=\frac{R_{si} \bullet R_{sf}}{R_{sf}-R_{si}}$
Sample	Rs	Rs	Rs	Rs_i	Rs_f	
#	(Ω/sq)	(Ω/sq)	(Ω/sq)	(Ω/sq)	(Ω/sq)	(Ω/sq)
M6	648.24	642.64	686.16	642.64	10132.09	686.16
M7	1409.3	1421.78	1615.03	1421.78	10922.99	1634.54
M9	1142.8	1144.51	1641.58	1144.51	4540.71	1530.21

Application of CAOT DHE For Doped Polysilicon Films (2)



Application of CAOT DHE For Doped Polysilicon Films (3)

Mobility in Doped Polysilicon Films

$$\mu_d = \frac{q\tau_{sc}}{m^*}$$

$$\tau_{sc} = \frac{1}{\sigma_{sc} N_{sc} v_{th}}$$

$\frac{1}{\sigma_{sc} N_{sc}}$ = Scattering length

τ_{sc} = Average scattering time

σ_{sc} = Scattering cross-section

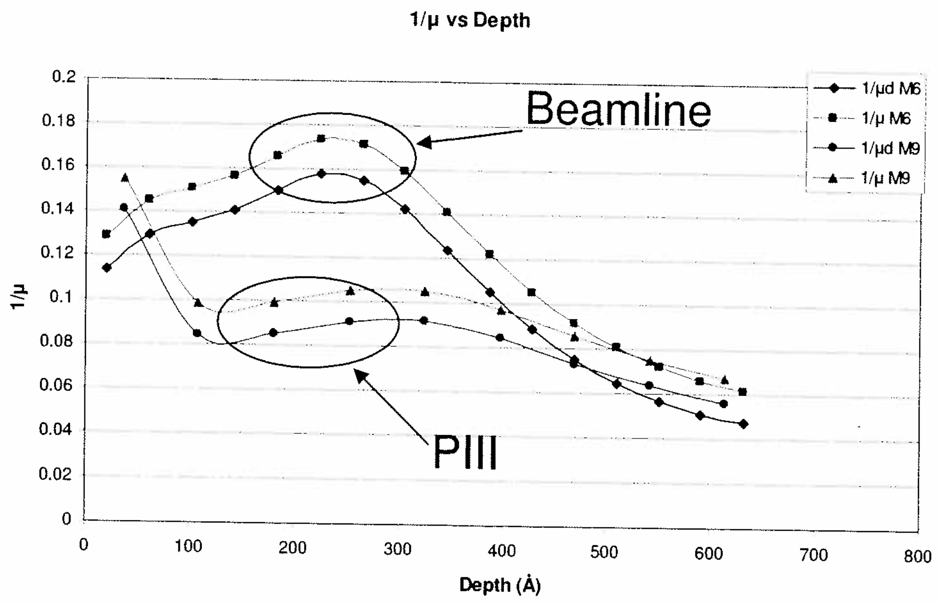
N_{sc} = Scattering centers/unit volume

v_{th} = Average thermal velocity

$$\mu_d = K\left(\frac{1}{\sigma_{sc} N_{sc}}\right)$$

Mobility is proportional to average distance that a carrier travels between two collisions, i.e. the average grain diameter for polysilicon.

Application of CAOT DHE For Doped Polysilicon Films (4)



The reciprocal mobility defect component dominates throughout the thickness of the doped polysilicon thickness. Since precipitates do not appear to affect the scattering phenomenon (13), the defect component must be attributed to the grain boundaries. Queirolo (14) has proposed a semi-quantitative relationship between the mean grain size and μ_d .

$$\mu_d = KD^{\alpha}$$

where K = 4.5E4 and α = 0.59 are constants
D (cm) = mean grain size.

Measurement Capabilities

- Accurate Carrier Concentrations up to the Surface
- Total Activated Dose
- Accurate Drift Mobilities
- Location and Magnitude of Scattering Defects
- Magnitude of Strain Enhanced Mobility
- Polysilicon Grain Size

Measurable Structures

- p+n , n+p USJ's
- Doped Polysilicon Films
- Processed SOI
- Strain Enhanced Mobility Layers

Contributions of CAOT

- 1. CAOT can be completely automated, allowing for push-button operation.
- 2. Time for a complete evaluation was greatly decreased, from hours to minutes.
- 3. Precision was increased, permitting atomic layer resolution, especially useful for surface evaluation.
- 4. Drift mobility profiles are obtainable.
- 5. Active dopant profiles can be obtained rather than the total dopant distribution obtained with SIMS.
- 6. Permits the evaluation of the magnitude and location of carrier de-activation and scattering defects

Conclusions

- The CAOT applied to DHE permits us to accurately evaluate ultra shallow junctions making it possible to also evaluate the higher carrier concentrations above 1E20 cm^{-3}.
- The distribution of the defect contribution to the mobility can be determined
- Comparison of the carrier concentration distribution below 1E20 cm^{-3} with the A.S.T.M. algorithm permits us to evaluate the accuracy of our measurements.
- For doped polysilicon films, it is possible to determine the carrier concentration distribution as well as the mobility scattering component distribution due to grain boundaries.
- The DHE data permits us to comparatively evaluate different doping and thermal annealing techniques.
- Potential to study strain enhanced mobility.